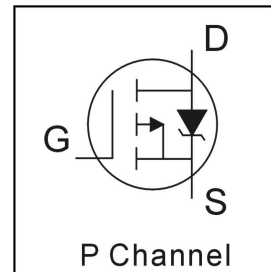


P Channel Power MOSFET

Chip Specification

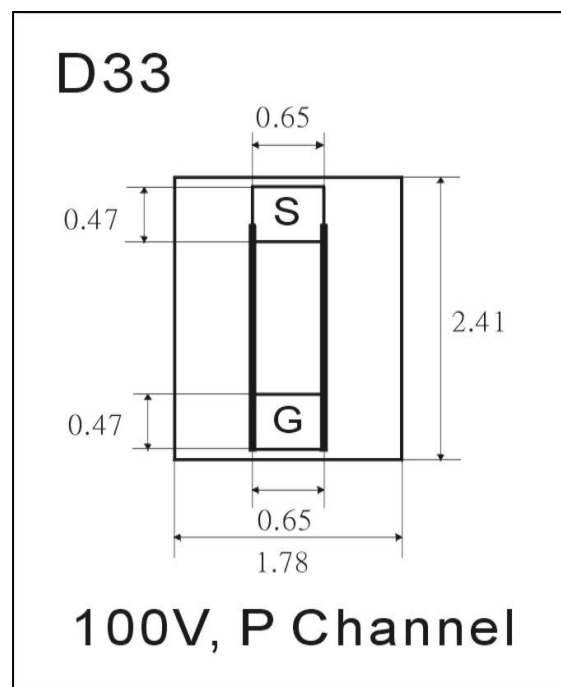
General Description:

- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * **175°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**



Mechanical Data:

D33	
Dimension	1.78mm x 2.41mm
Thickness:	400 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
95/5 PbSn or 92.5/2.5/5 PbAgIn	
Source Bonding Wire:	5 mil Al



Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	-V(BR)DSS	100	V	- VGS=0V, -ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	1.2	Ω	- VGS=10V,- ID=2.4A
Continuous Drain current (in target package)	-ID@25°C	4	A	- VGS=10V
Continuous Drain current (in target package)	-ID@100°C	2.8	A	- VGS=10V
Operation Junction Temperatre	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

Target Device: IRF9510

TO-220AB

Pd

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W

@Tc=25°C

